

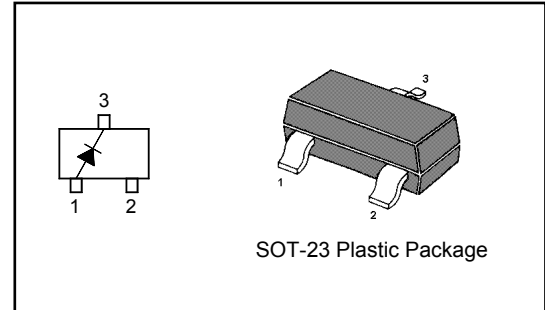
BAS16 Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching application



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4	A
		$t = 1\ \mu\text{s}$	
		$t = 1\ \text{ms}$	
	$t = 1\ \text{s}$	0.5	
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V_F	-	715	mV
at $I_F = 1\ \text{mA}$			855	mV
at $I_F = 10\ \text{mA}$			1	V
at $I_F = 150\ \text{mA}$			1.25	V
Reverse Current	I_R	-	30	nA
at $V_R = 25\ \text{V}$			1	μA
at $V_R = 75\ \text{V}$			30	μA
at $V_R = 25\ \text{V}, T_J = 150\text{ }^\circ\text{C}$			50	μA
at $V_R = 75\ \text{V}, T_J = 150\text{ }^\circ\text{C}$				
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V
at $I_R = 100\ \mu\text{A}$				
Diode Capacitance	C_d	-	2	pF
at $V_R = 0, f = 1\ \text{MHz}$				
Reverse Recovery Time	t_{rr}	-	4	ns
at $I_F = I_R = 10\ \text{mA}, R_L = 50\ \Omega$				

Typical Characteristics

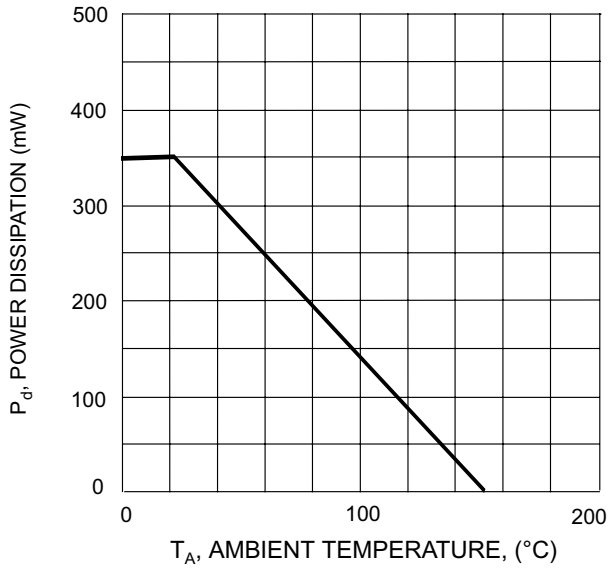


Fig. 1 Power Derating Curve

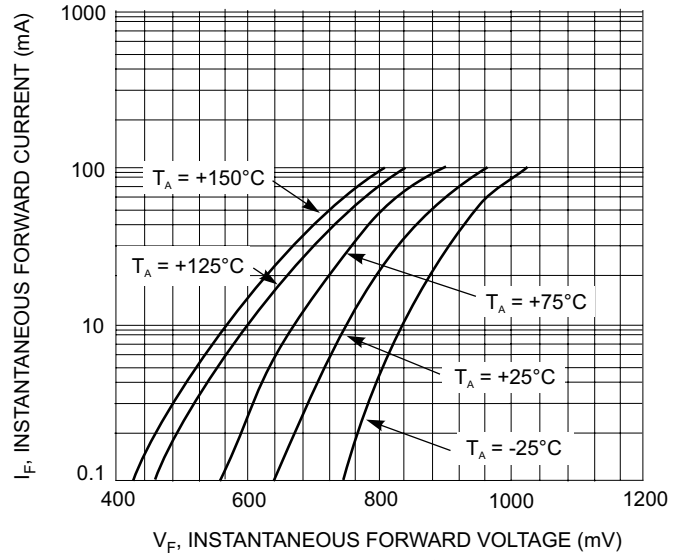


Fig. 2, Typical Forward Characteristics

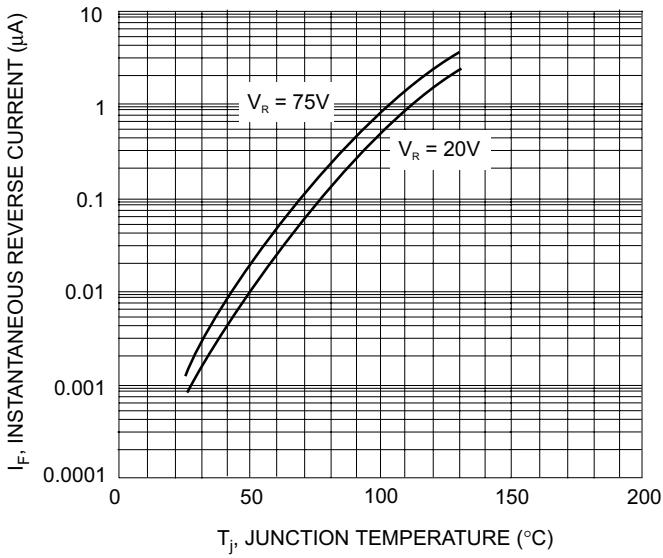
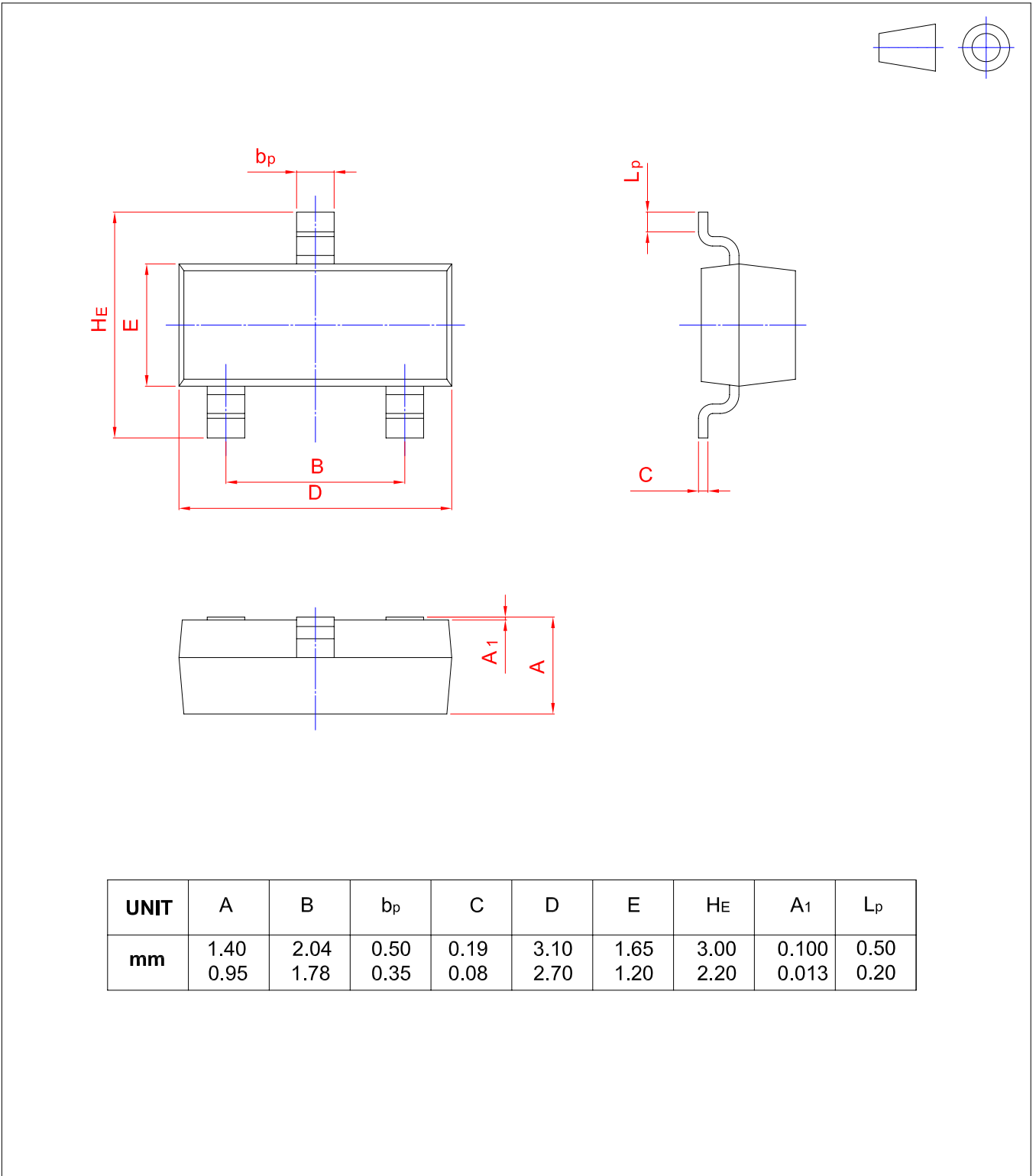


Fig. 3, Typical Reverse Characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



单击下面可查看定价，库存，交付和生命周期等信息

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